Features :

- Isolated mounting base 3000V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

Typical Applications

- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

V_{DSM},V_{RSM}	V_{DRM},V_{RRM}	品名
900V	800V	Mx800TH80
1100V	1000V	Mx800TH100
1300V	1200V	Mx800TH120
1500V	1400V	Mx800TH140
1700V	1600V	Mx800TH160
1900V	1800V	Mx800TH180

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j(℃)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Single side cooled,T_c=85℃	125			800	A
$I_{T(RMS)}$	RMS on-state current					1256	A
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	125			45	mA
I_{TSM}	Surge on-state current	10ms half sine wave V_R=0.6V_{RRM}	125			22.0	kA
I^2t	I^2t for fusing coordination					2420	A^2s*10^3
V_{TO}	Threshold voltage		125			0.80	V
r_T	On-state slope resistance					0.20	mΩ
V_{TM}	Peak on-state voltage	I_{TM}=2400A	25			1.86	V
dv/dt	Critical rate of rise of off-state voltage	V_{DM}=67%V_{DRM}	125			1000	V/μs
di/dt	Critical rate of rise of on-state current	I_{TM} =1600A, Gate source 1.5A t_r ≤0.5μs Repetitive	125			200	A/μs
I_{GT}	Gate trigger current	V_A=12V, I_A=1A	25	30		200	mA
V_{GT}	Gate trigger voltage			1.0		3.0	V
I_H	Holding current			20		200	mA
V_{GD}	Non-trigger gate voltage	V_{DM}=67%V_{DRM}	125	0.2			V
$R_{th(j-c)}$	Thermal resistance Junction to case	Single side cooled per chip				0.042	℃/W
$R_{th(c-h)}$	Thermal resistance case to heatsink	Single side cooled per chip				0.020	℃/W
V_{iso}	Isolation voltage	50Hz,R.M.S,t=1min,I_{iso}:1mA(MAX)		3000			V
F_m	Terminal connection torque(M12)				14.0		N·m
	Mounting torque(M8)				12.0		N·m
T_{vj}	Junction temperature			-40		125	℃
T_{stg}	Stored temperature			-40		125	℃
W_t	Weight				3240		g
Outline	M07						

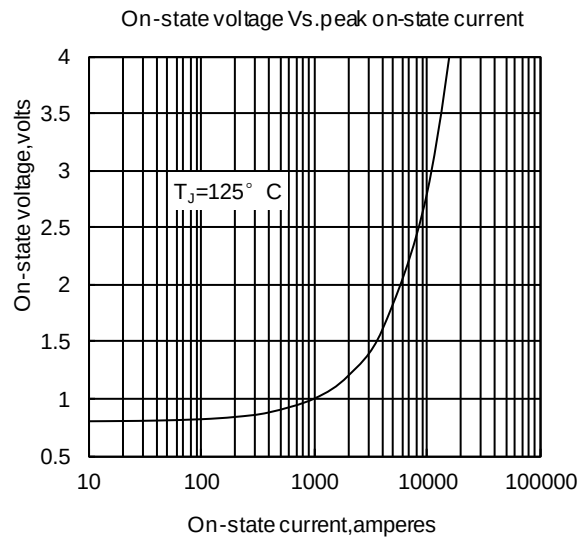


Fig1

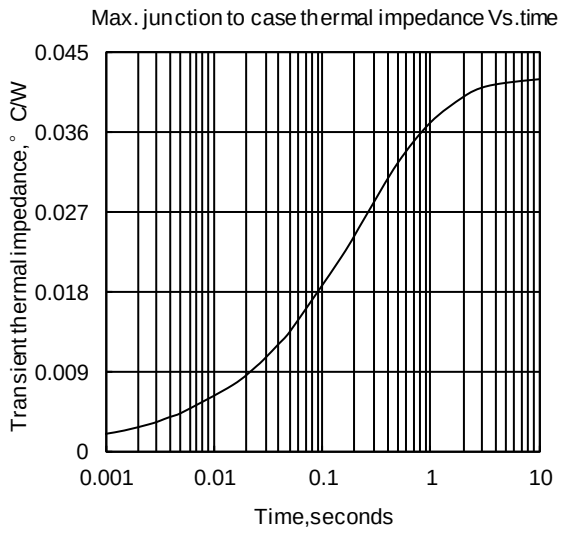


Fig2

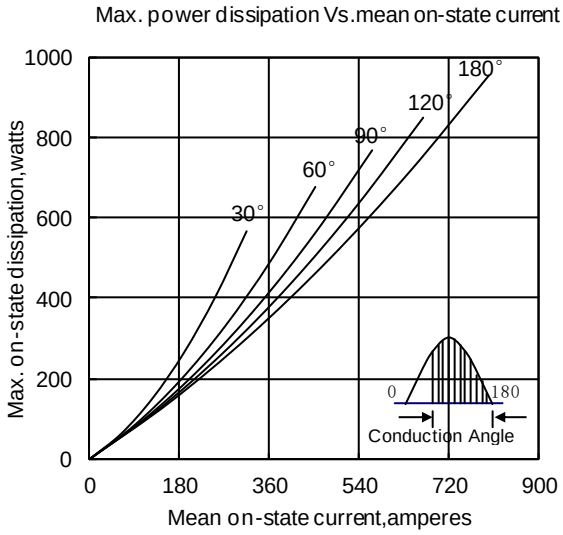
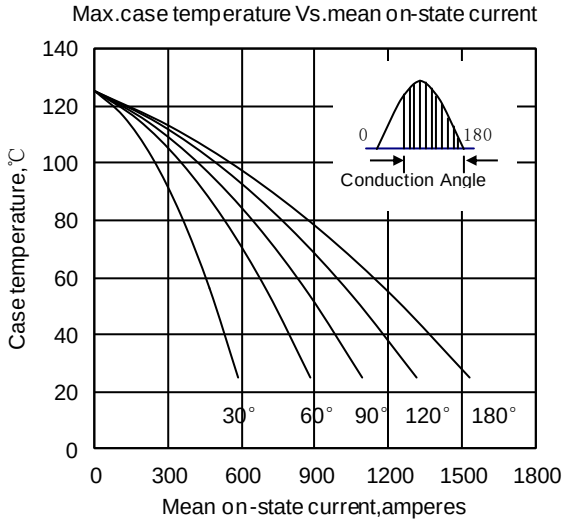


Fig3



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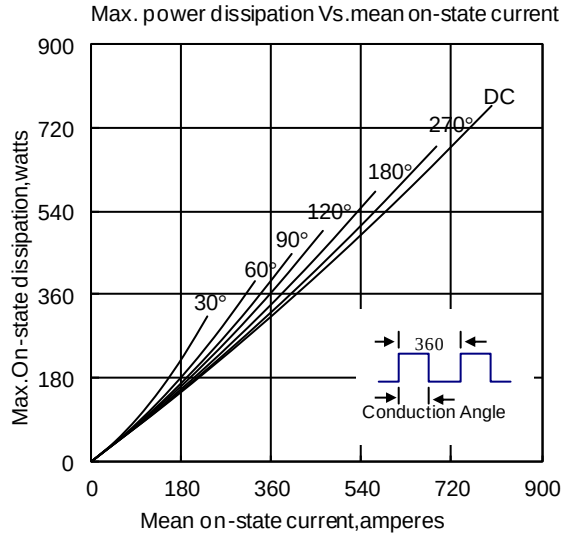

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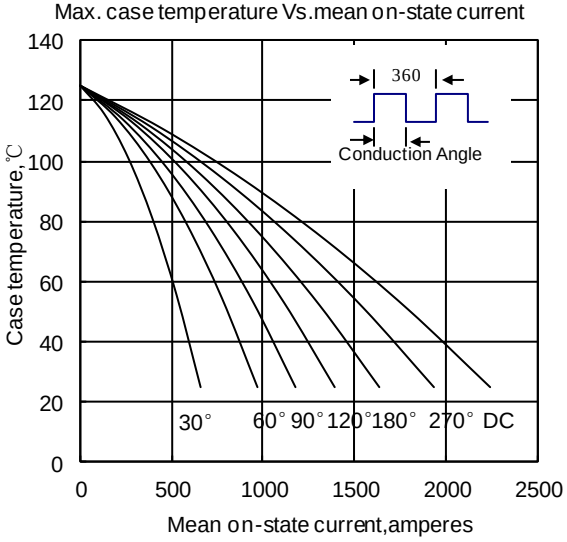

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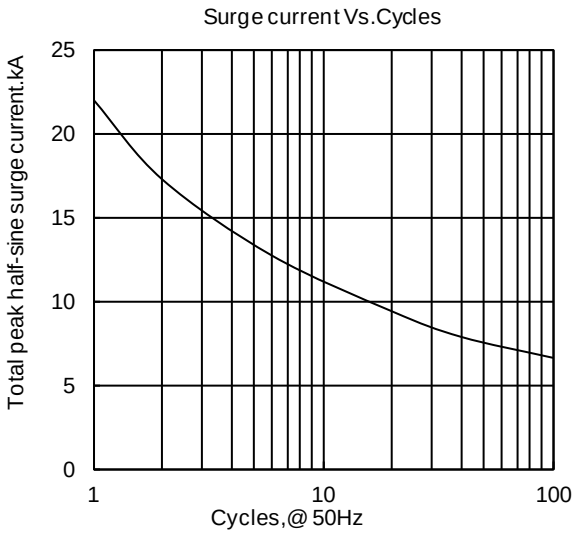

Fig7

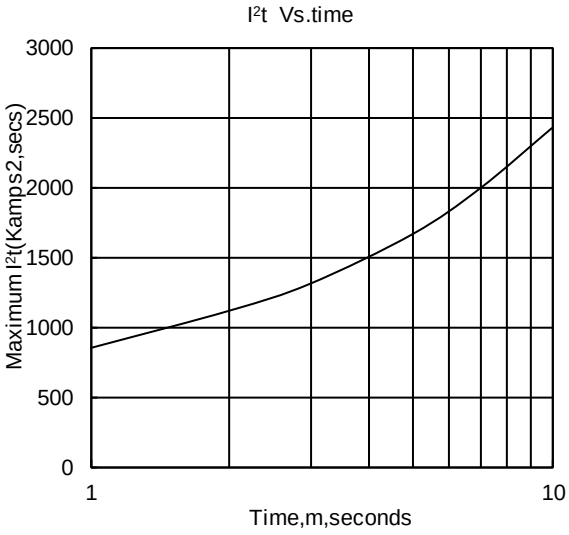

Fig8

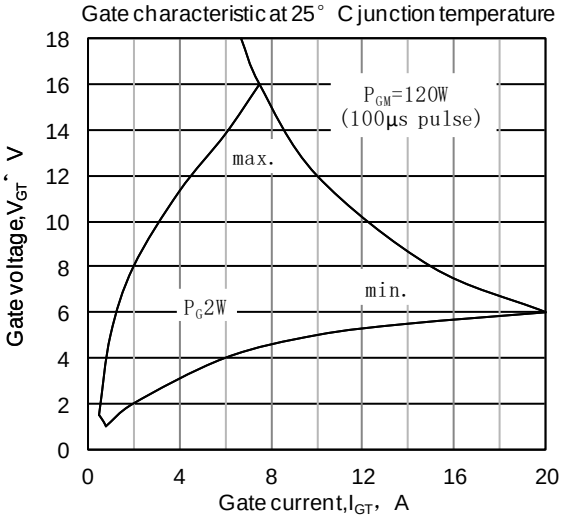

Fig9

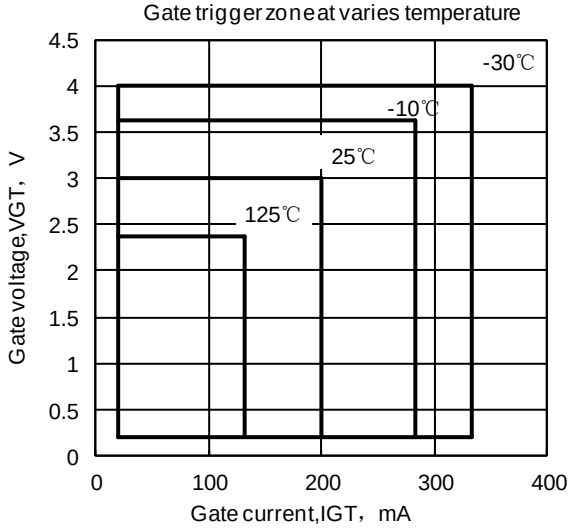
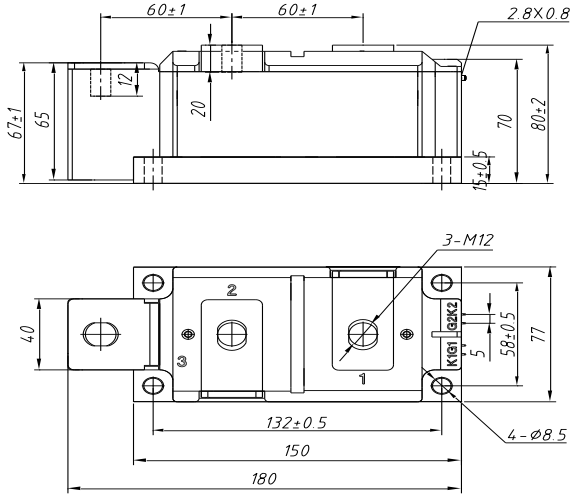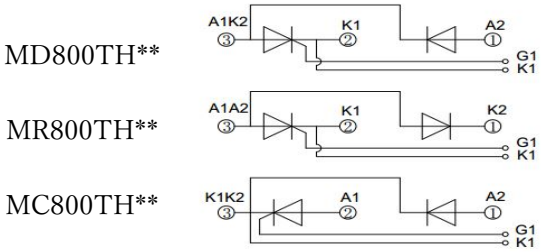
Fig10